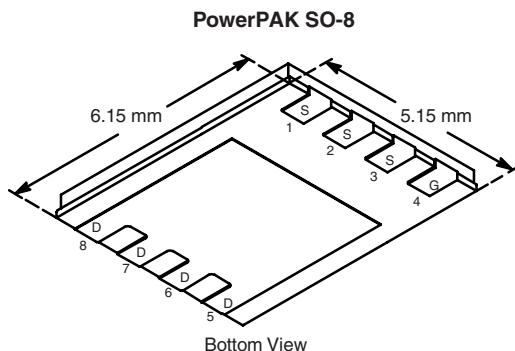


N-Channel 250-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
250	0.155 at $V_{GS} = 10$ V	3.8
	0.162 at $V_{GS} = 6$ V	3.7

FEATURES

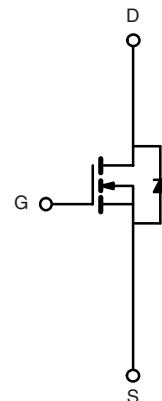
- Halogen-free According to IEC 61249-2-21 Available
- PWM-OptimizedTrenchFET® Power MOSFET
- 100 % R_g Tested
- Avalanche Tested



Ordering Information: Si7434DP-T1-E3 (Lead (Pb)-free)
Si7434DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

APPLICATIONS

- Primary Side Switch In:
 - Telecom Power Supplies
 - Distributed Power Architectures
 - Miniature Power Modules



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	10 s	Steady State	Unit
Drain-Source Voltage	V_{DS}	250		V
Gate-Source Voltage	V_{GS}			
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	3.8	2.3	A
		3.0	1.8	
Pulsed Drain Current	I_{DM}	40		A
Continuous Source Current (Diode Conduction) ^a	I_S	4.3	1.6	
Avalanche Current	I_{AS}	13		mJ
Single Pulse Avalanche Energy	E_{AS}	8.4		
Maximum Power Dissipation ^a	P_D	5.2	1.9	W
		3.3	1.2	
Operating Junction and Storage Temperature Range	T_J , T_{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b,c}		260		

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ s	19	24	°C/W
	Steady State	52	65	
Maximum Junction-to-Case (Drain)	R_{thJC}	1.5	1.8	

Notes:

- Surface Mounted on 1" x 1" FR4 board.
- See Solder Profile (www.vishay.com/ppg?73257). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted

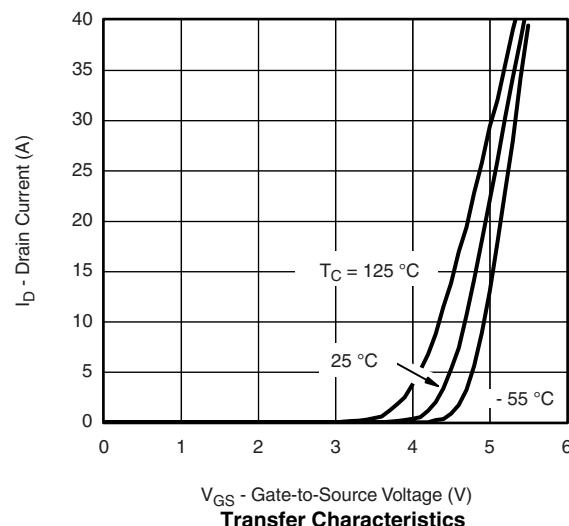
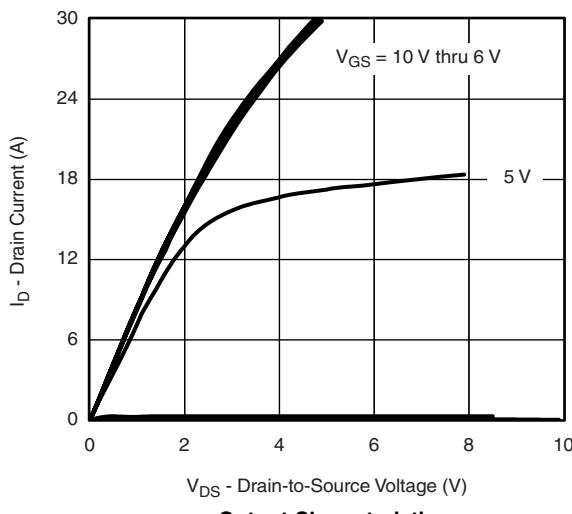
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	2.0		4.0	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 250 \text{ V}$, $V_{GS} = 0 \text{ V}$		1		μA
		$V_{DS} = 250 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 55^\circ\text{C}$			15	
On-State Drain Current ^a	$I_{D(\text{on})}$	$V_{DS} \geq 5 \text{ V}$, $V_{GS} = 10 \text{ V}$	30			A
Drain-Source On-State Resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$, $I_D = 3.8 \text{ A}$		0.129	0.155	Ω
		$V_{GS} = 6.0 \text{ V}$, $I_D = 3.7 \text{ A}$		0.131	0.162	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15 \text{ V}$, $I_D = 3.8 \text{ A}$		14		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.8 \text{ A}$, $V_{GS} = 0 \text{ V}$		0.75	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 100 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 3.8 \text{ A}$		34	50	nC
Gate-Source Charge	Q_{gs}			6.8		
Gate-Drain Charge	Q_{gd}			10.5		
Gate Resistance	R_g		0.6	1.2	1.8	Ω
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = 100 \text{ V}$, $R_L = 25 \Omega$ $I_D \geq 4.0 \text{ A}$, $V_{GEN} = 10 \text{ V}$, $R_g = 6 \Omega$		16	25	ns
Rise Time	t_r			23	35	
Turn-Off Delay Time	$t_{d(\text{off})}$			47	70	
Fall Time	t_f			19	30	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.8 \text{ A}$, $dI/dt = 100 \text{ A}/\mu\text{s}$		100	150	

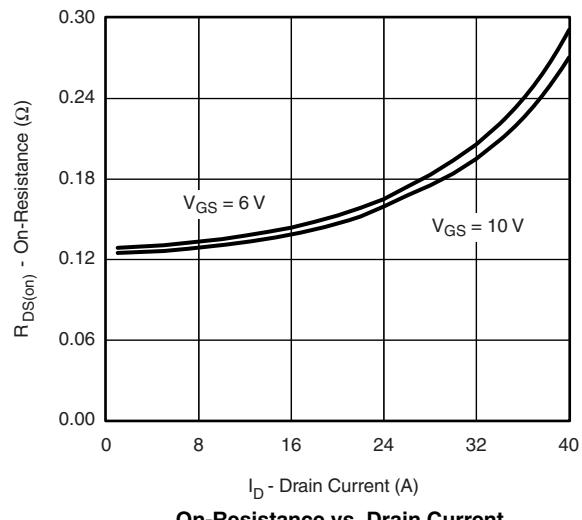
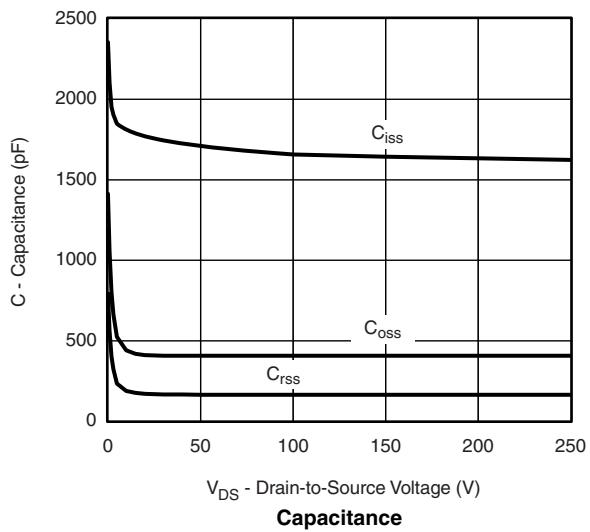
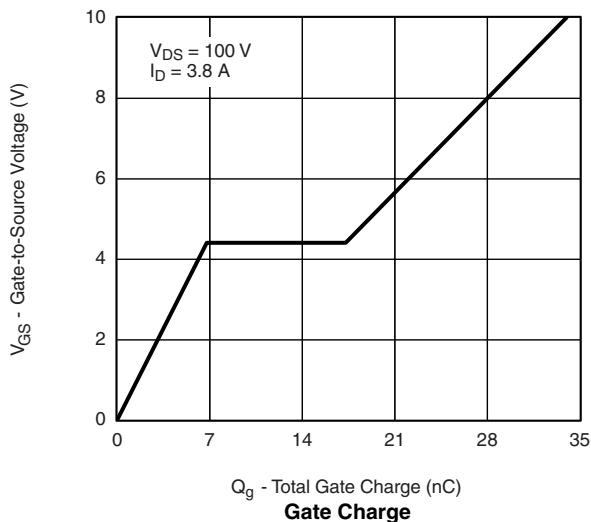
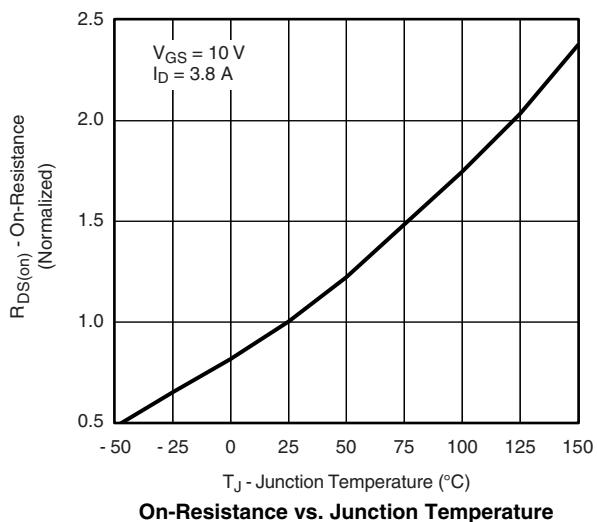
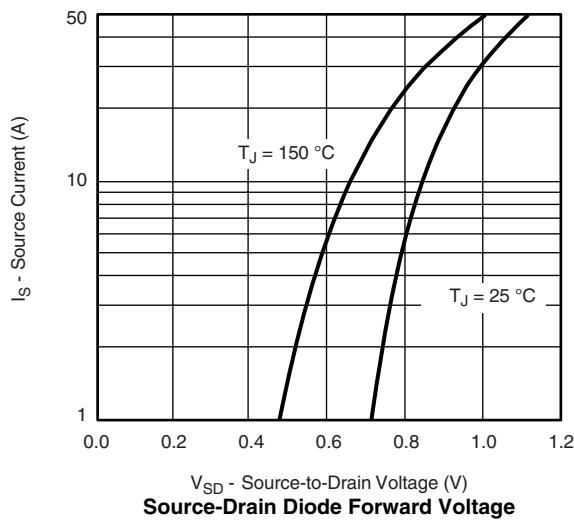
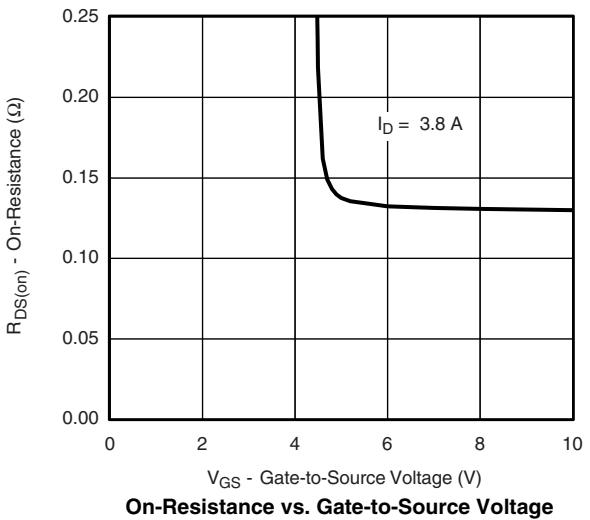
Notes

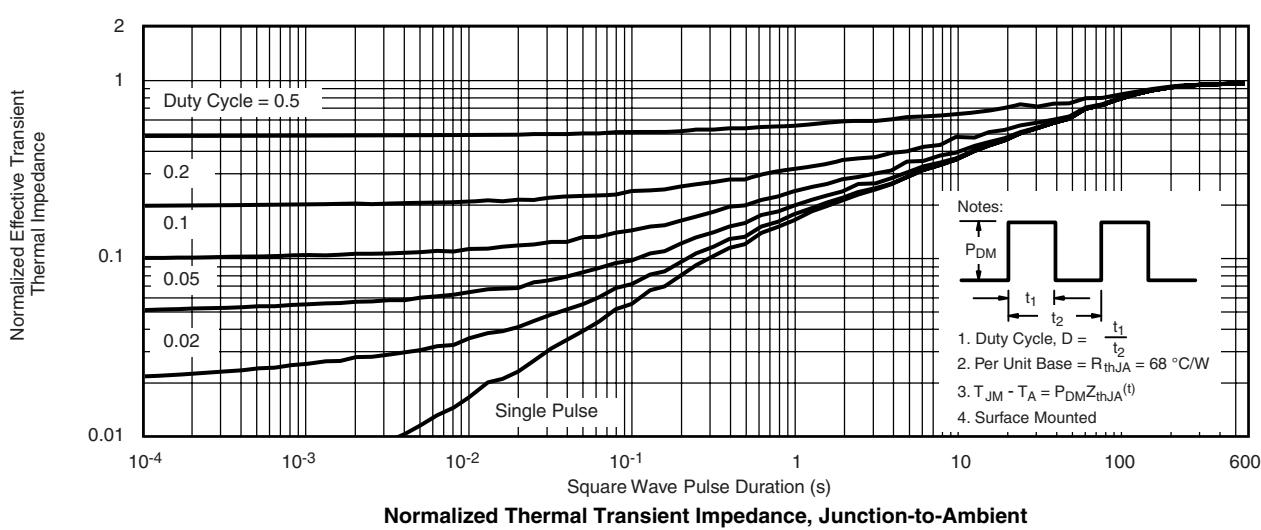
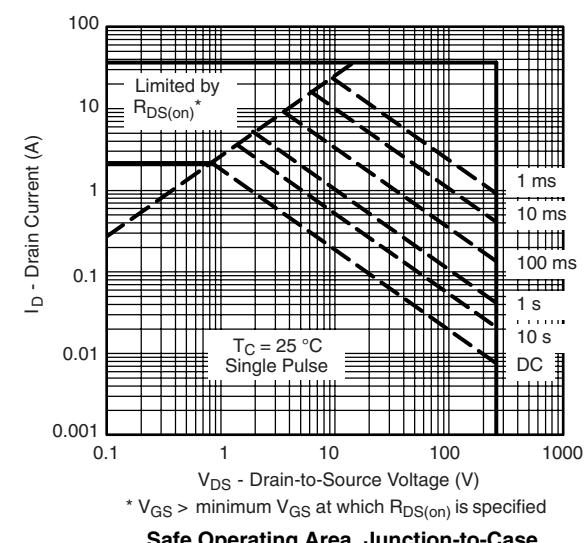
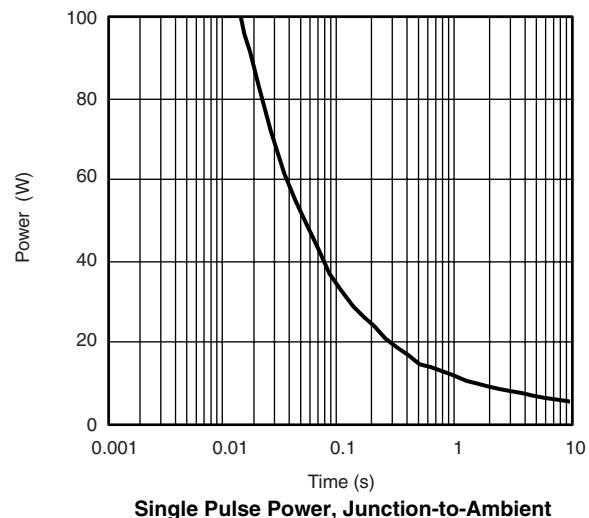
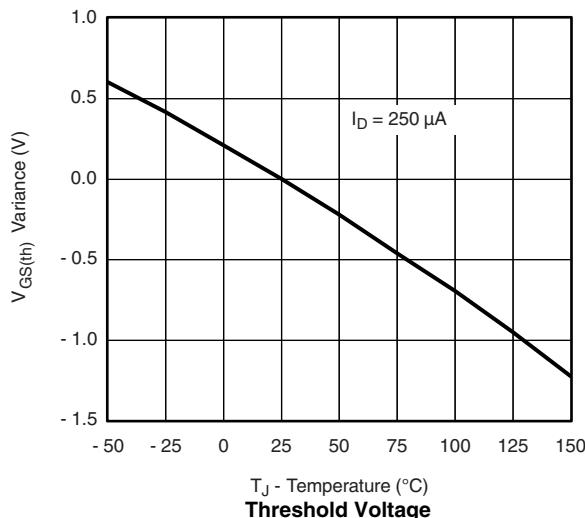
a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.

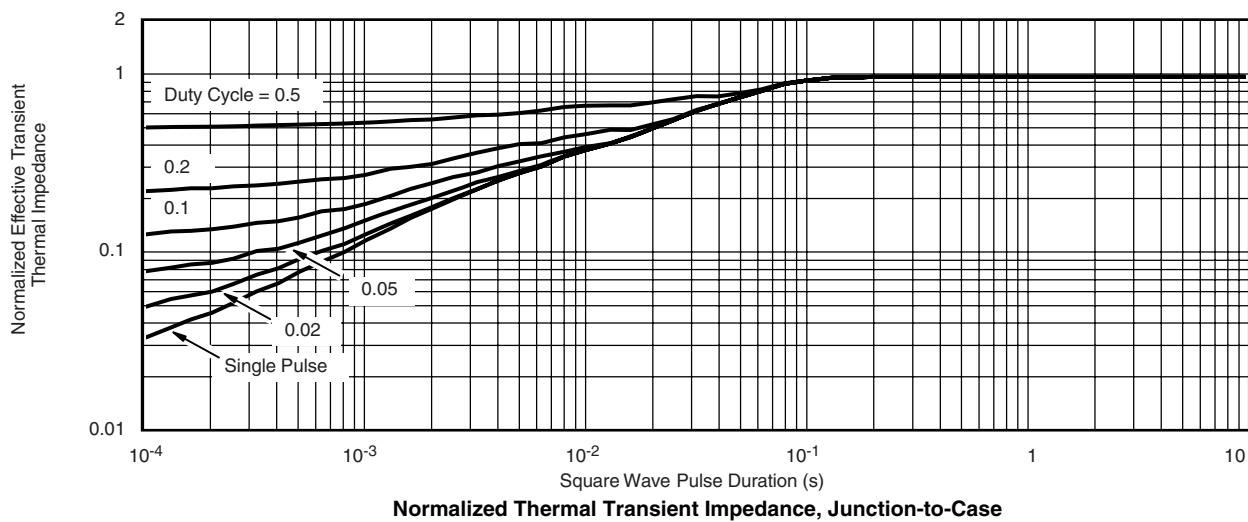
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25°C , unless otherwise noted


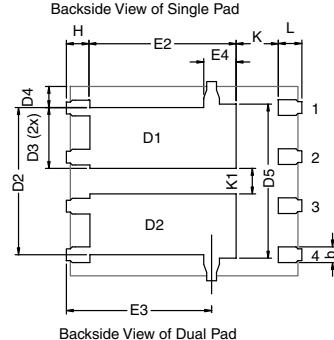
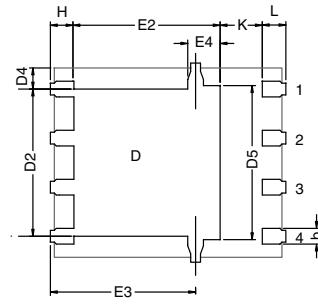
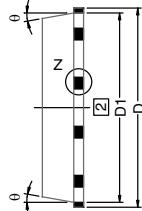
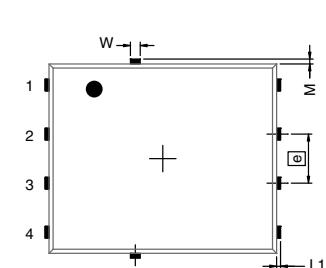
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72579.

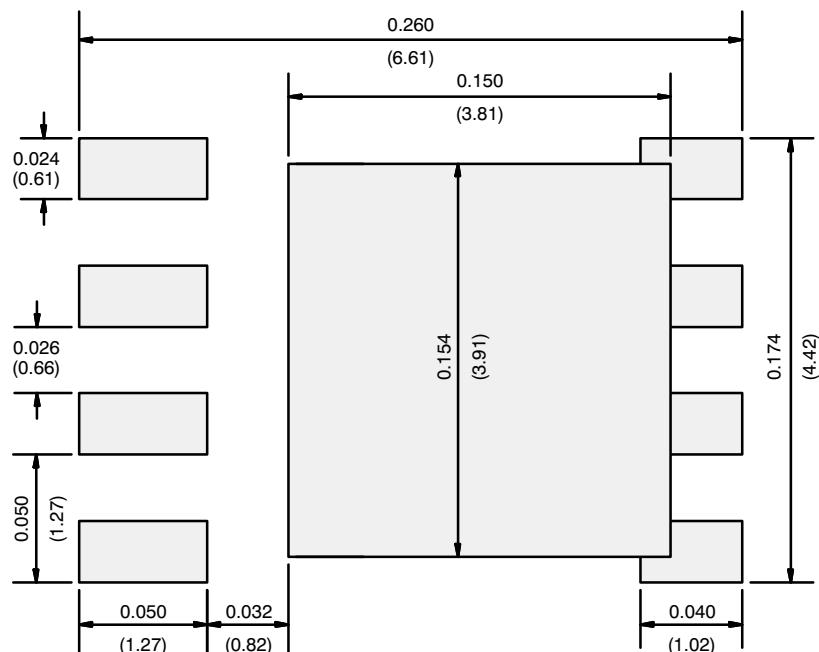
PowerPAK® SO-8, (Single/Dual)


Notes

1. Inch will govern.
2. Dimensions exclusive of mold gate burrs.
3. Dimensions exclusive of mold flash and cutting burrs.

DIM.	MILLIMETERS			INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
A	0.97	1.04	1.12	0.038	0.041	0.044	
A1		-	0.05	0	-	0.002	
b	0.33	0.41	0.51	0.013	0.016	0.020	
c	0.23	0.28	0.33	0.009	0.011	0.013	
D	5.05	5.15	5.26	0.199	0.203	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.56	3.76	3.91	0.140	0.148	0.154	
D3	1.32	1.50	1.68	0.052	0.059	0.066	
D4	0.57 typ.			0.0225 typ.			
D5	3.98 typ.			0.157 typ.			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	5.79	5.89	5.99	0.228	0.232	0.236	
E2 (for AL product)	3.30	3.48	3.66	0.130	0.137	0.144	
E2 (for other product)	3.48	3.66	3.84	0.137	0.144	0.151	
E3	3.68	3.78	3.91	0.145	0.149	0.154	
E4 (for AL product)	0.58 typ.			0.023 typ.			
E4 (for other product)	0.75 typ.			0.030 typ.			
e	1.27 BSC			0.050 BSC			
K (for AL product)	1.45 typ.			0.057 typ.			
K (for other product)	1.27 typ.			0.050 typ.			
K1	0.56	-	-	0.022	-	-	
H	0.51	0.61	0.71	0.020	0.024	0.028	
L	0.51	0.61	0.71	0.020	0.024	0.028	
L1	0.06	0.13	0.20	0.002	0.005	0.008	
θ	0°	-	12°	0°	-	12°	
W	0.15	0.25	0.36	0.006	0.010	0.014	
M	0.125 typ.			0.005 typ.			

ECN: C13-0702-Rev. K, 20-May-13
DWG: 5881

RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Single

Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)

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